

AMENDMENTS

Please amend the application as indicated hereafter.

To the Claims:

Claim 1. (currently amended) A semiconductor cleaning method, comprising:  
providing a semiconductor wafer;  
forming a first layer of oxide over the semiconductor wafer;  
forming a floating gate layer over the first layer of oxide;  
forming a second layer of oxide over the floating gate layer;  
etching the first layer of oxide, the floating gate layer, and the second layer of oxide to form a gate structure;  
~~cleaning rinsing~~ the semiconductor wafer including the gate structure using an ozonated de-ionized (DI) water;  
further cleaning [[of ]]the ozonated water~~cleaned rinsed~~ semiconductor wafer using a first cleaning solution, wherein the first cleaning solution is a HF:HCl:H<sub>2</sub>O solution or at least one of H<sub>2</sub>O:H<sub>2</sub>O<sub>2</sub>:NH<sub>4</sub>OH solution and H<sub>2</sub>O:H<sub>2</sub>O<sub>2</sub>:HCl solution; and  
additionally cleaning [[of ]]the further cleaned semiconductor wafer using a second cleaning solution the ozonated DI water.

Claim 2. (original) The method of claim 1, wherein the floating gate comprises polysilicon or nitride.

Claim 3. (original) The method of claim 1, wherein the semiconductor wafer has

formed therein at least one device.

Claim 4. (original) The method of claim 1, wherein the semiconductor wafer has accumulated thereon contaminants accumulated during at least one previous processing step.

Claim 5. (previously presented) The method of claim 4, wherein the contaminants comprise polymer.

Claim 6. (original) The method of claim 5, wherein the polymer comprises photoresist.

Claim 7. (currently amended) The method of claim 1, wherein the first cleaning solution comprises [[a]]the H<sub>2</sub>O:H<sub>2</sub>O<sub>2</sub>:NH<sub>4</sub>OH solution, wherein and the proportions of H<sub>2</sub>O:H<sub>2</sub>O<sub>2</sub>:NH<sub>4</sub>OH are within the range of [[1]]4-80:1-5:[[4-80]]1.

Claim 8. (currently amended) The method of claim 7, wherein the proportions of H<sub>2</sub>O:H<sub>2</sub>O<sub>2</sub>:NH<sub>4</sub>OH are [[2.1]]80:3.1:[[80]]2.1.

Claim 9. (withdrawn and currently amended) The method of claim 1, wherein the first cleaning solution comprises [[a]]the H<sub>2</sub>O:H<sub>2</sub>O<sub>2</sub>:HCl solution, wherein and the proportions of H<sub>2</sub>O:H<sub>2</sub>O<sub>2</sub>:HCl are within the range of [[1]]4-80:1-5:[[4-80]]1.

Claim 10. (withdrawn and currently amended) The method of claim 9, wherein the proportions of H<sub>2</sub>O:H<sub>2</sub>O<sub>2</sub>:HCl are [[1.3]]80:2.2:[[ 80]]1.3.

Claim 11. (withdrawn and currently amended) The method of claim 1, wherein the first cleaning solution comprises [[a]]the HF:HCl:H<sub>2</sub>O solution, wherein and the proportions of HF:HCl:H<sub>2</sub>O are 1:1.3:400.

Claim 12. (original) The method of claim 1, wherein the concentration of ozone in the ozonated DI water is within the range of 10-80 ppm.

Claim 13. (original) The method of claim 12, wherein the concentration of ozone in the ozonated DI water is 40 ppm.

**Claims 14-20. (canceled)**